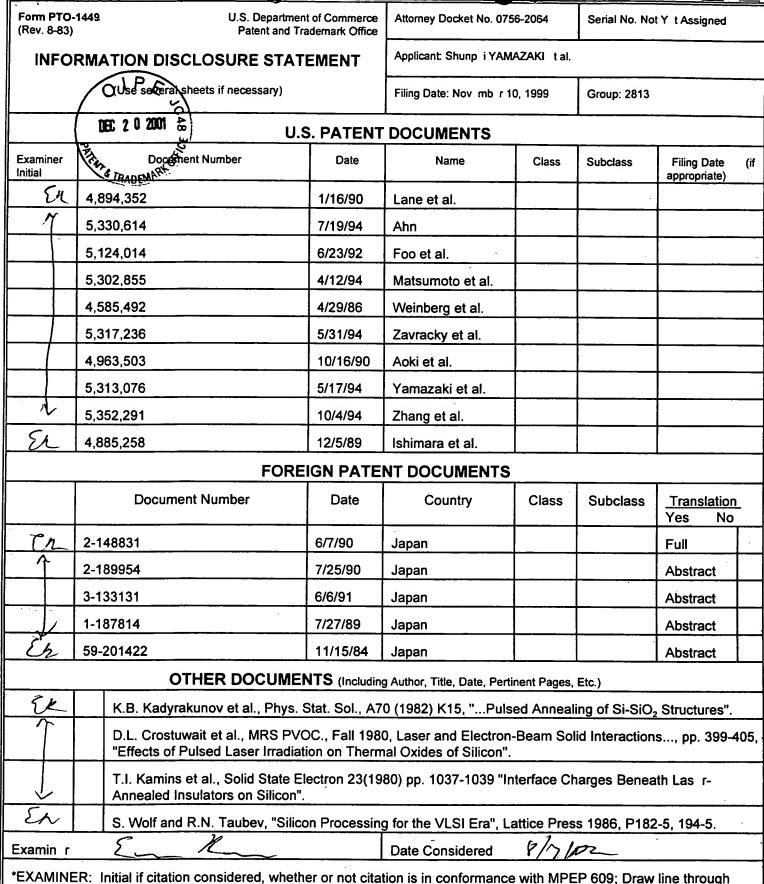
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- EjL	5,773,325	6/1998	Teramoto	438	151				
1	5,237,188	8/17/93	lwai	257	325	†			
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	4,851,370	7/25/89	Doklan et al.	437	225				
	5,476,802	12/19/95	Yamazaki et al.	437	21				
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EL	5,700,333	12/23/97	Yamazaki et al.	136	258				
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ZK.	1-149475	6/12/89	Japan			Abstract	Ť		
	1-128572	5/22/89	Japan			Abstract	+		
	61-89621	5/7/86	Japan			Abstract	+		
	61-166074	7/26/86	Japan			Abstract	1		
	0 178 447	4/23/86	Europe			Full & Abstract			
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El	3-203329	9/5/91	Japan			Abstract	†		
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EX	C. Hayzelden et al.	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) C. Hayzelden et al. "In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon", (3 pages), Published 10/29/91.							
EK	S. Wolf, "Silicon Processing for the VLSI Era" Vol. 3, Pages 658-60, 671-72, 1995.								
Sh	Translation of JP 2-		,	0, 0, 1-12,	1030.				
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ER	5,147,826	9/15/92	Liu et al.	437	233			
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	4,810,673	3/7/89	Freeman	437	239			
	5,225,355	7/6/93	Sugino et al.	437	10			
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Er	61-63020	4/1/86	Japan	,a.		Abstract	T	
7	2-140915	5/30/90	Japan			Abstract		
	2-295111	12/6/90	Japan			Abstract		
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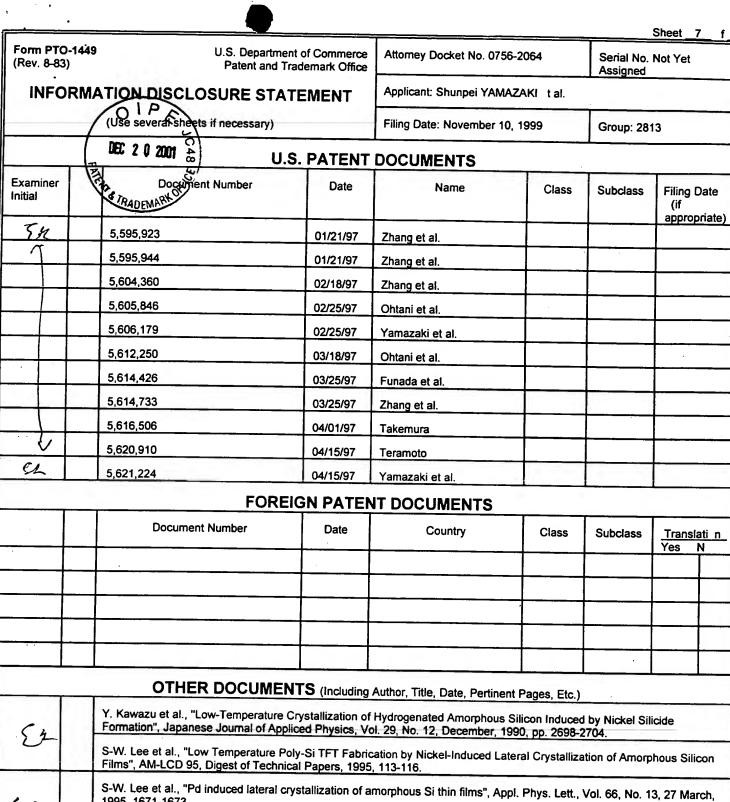
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U	5,330,929	7/19/94	Pfiester et al.					
7	5,308,998	5/3/94	Yamazaki et al.					
	5,313,075	5/17/94	Zhang et al.					
V	5,278,093	1/11/94	Yonehara	·				
8h	4,784,975	11/15/88	Hoffman et al.					
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CK	·	Kugimiya, K. et al., Japanese Journal of Applied Phy. 22(1)1982, P. L19-L21, "CW laser annealing of".						
En	Japanese J. of Appl. Phys.,							
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ĵ	4,727,044	02/23/88	Yamazaki		†	+	
	5,010,037	04/23/91	Lin et al.			+	
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Eh	5,492,843	02/20/96	Adachi et al.				
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EX	58-190020	11/05/83	Japan		. 1	Abstract	Τ
	05-58789	03/09/93	Japan			Abstract	+
	62-33417	02/13/87	Japan			Abstract	+
	55-153339	11/29/80	Japan			Abstract	+
ER	4-284675	12.02.00	Japan	7		Abstract	+
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	S.F. Gong et al. "Thermodynar Binary Systems" J. Appl. Phys	mic Investigations s. 68(9), 1 Novem	s of Solid-state Si-metla In ther 1990, 4542-4549.	iteractions.II. G	Seneral Analy	sis of Si-met	tal
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SK	5,501,989	03/26/96	Takayama et al.			(ii appropriate)		
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EL	64-37029	02/07/89	Japan			Abstract		
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C1.	C. Hayzelden et al. "In situ transmiss (3 pages).	C. Hayzelden et al. "In situ transmission electron microscopy studies of silicide-mediated crystallization of amorphous silicon", (3 pages).						
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EL .	5,624,851	04/29/97	Takayama et al.	-	+	appropriate)
1	5,637,515	06/10/97	Takemura		+	
	5,643,826	07/01/97	Ohtani et al.		-	+
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	5,656,825	08/12/97	Kusumoto et al.		+	
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